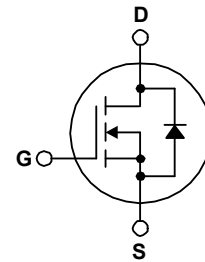
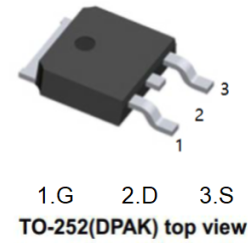


Description

This N-Channel enhancement mode power MOSFET is planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- $V_{DS} = 100V$
- $R_{DS(ON)}(at\ V_{GS}=10V) < 350m\Omega$
- $I_D(at\ V_{GS}=10V) 2.9A$
- Low Gate Charge (Typ. 4.6 nC)
- Low C_{rss} (Typ. 12 pF)



Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted.

Symbol	Parameter	FQD7N10LTM	Unit
V_{DSS}	Drain-Source Voltage	100	V
I_D	Drain Current - Continuous ($T_C = 25^\circ C$)	5.8	A
	- Continuous ($T_C = 100^\circ C$)	3.67	A
I_{DM}	Drain Current - Pulsed (Note 1)	23.2	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	50	mJ
I_{AR}	Avalanche Current (Note 1)	5.8	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns
P_D	Power Dissipation ($T_A = 25^\circ C$) *	2.5	W
	Power Dissipation ($T_C = 25^\circ C$)	25	W
	- Derate above $25^\circ C$	0.2	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ C$

Thermal Characteristics

Symbol	Parameter	FQD7N10LTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	5.0	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.1		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100 V, V _{GS} = 0 V			1	μA
		V _{DS} = 80 V, T _C = 125°C			10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1.0		2.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 2.9 A V _{GS} = 5 V, I _D = 2.9 A		275 300	35 38	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 30 V, I _D = 2.9 A		4.6		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		220	290	pF
C _{oss}	Output Capacitance			55	72	pF
C _{rss}	Reverse Transfer Capacitance			12	15	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50 V, I _D = 7.3 A, R _G = 25 Ω (Note 4)		9	30	ns
t _r	Turn-On Rise Time			100	210	ns
t _{d(off)}	Turn-Off Delay Time			17	45	ns
t _f	Turn-Off Fall Time			50	110	ns
Q _g	Total Gate Charge	V _{DS} = 80 V, I _D = 7.3 A, V _{GS} = 5 V (Note 4)		4.6	6.0	nC
Q _{gs}	Gate-Source Charge			1.0		nC
Q _{gd}	Gate-Drain Charge			2.6		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current				5.8	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				23.2	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 5.8 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 7.3 A, dI _F / dt = 100 A/μs		70		ns
Q _{rr}	Reverse Recovery Charge			140		nC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 2.23 mH, I_{AS} = 5.8 A, V_{DD} = 25 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 7.3 A, di/dt ≤ 300 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

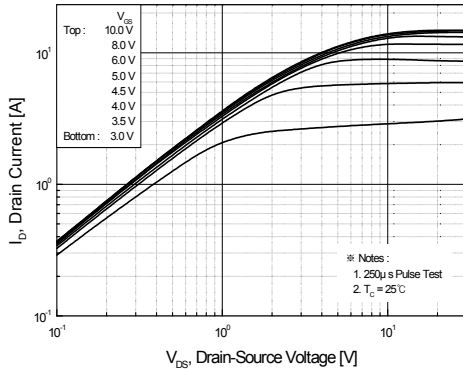


Figure 1. On-Region Characteristics

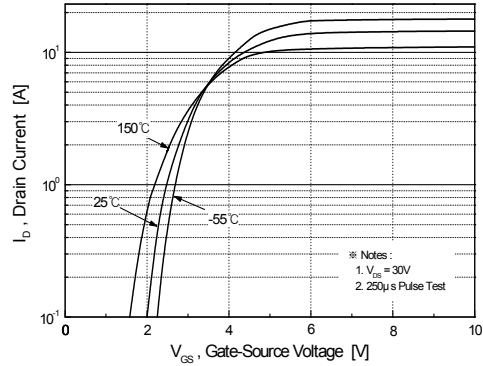


Figure 2. Transfer Characteristics

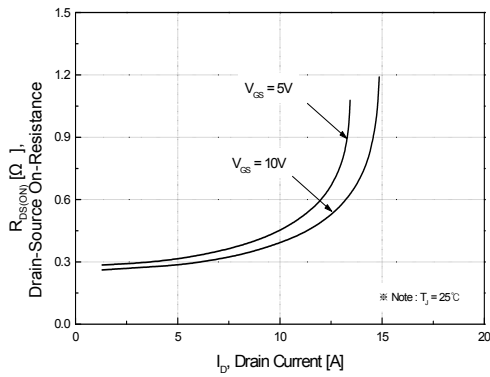


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

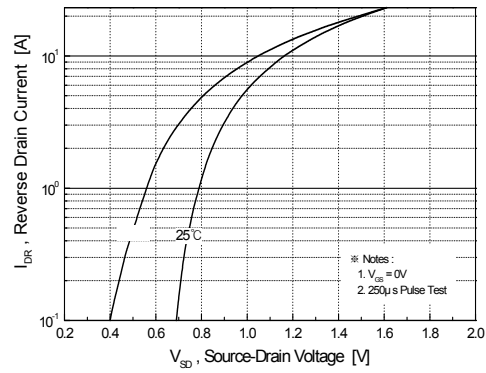


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

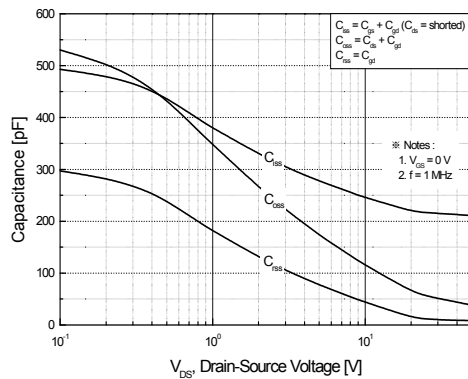


Figure 5. Capacitance Characteristics

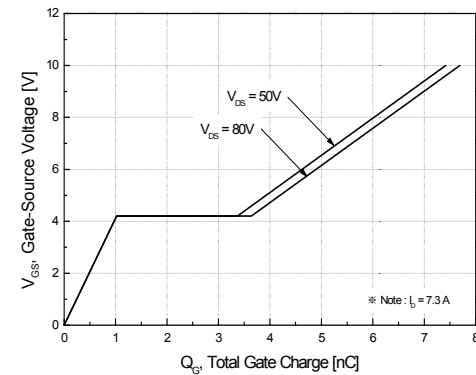


Figure 6. Gate Charge Characteristics

Typical Characteristics

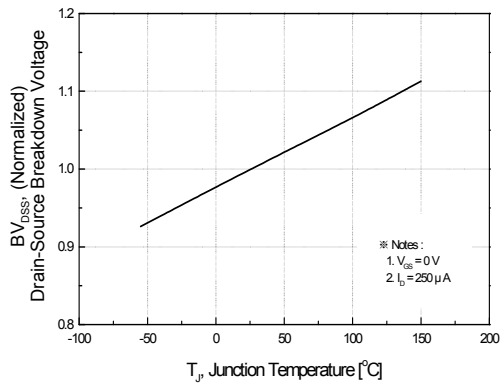


Figure 7. Breakdown Voltage Variation vs. Temperature

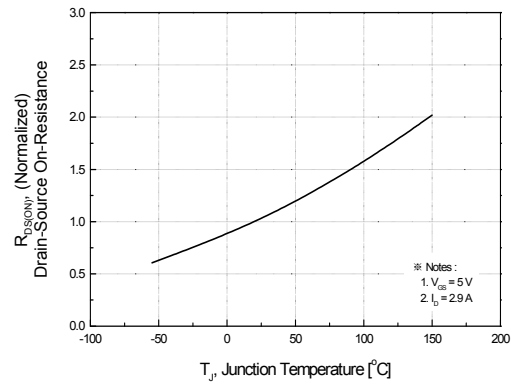


Figure 8. On-Resistance Variation vs. Temperature

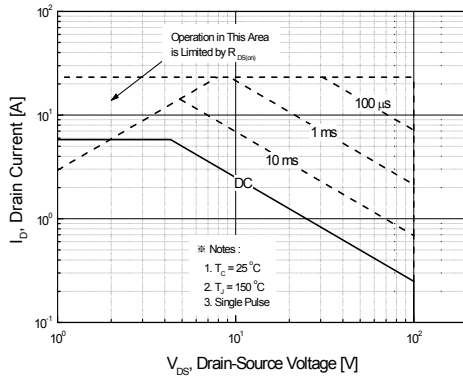


Figure 9. Maximum Safe Operating Area

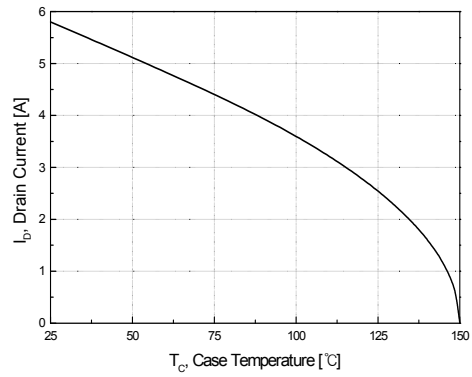


Figure 10. Maximum Drain Current vs. Case Temperature

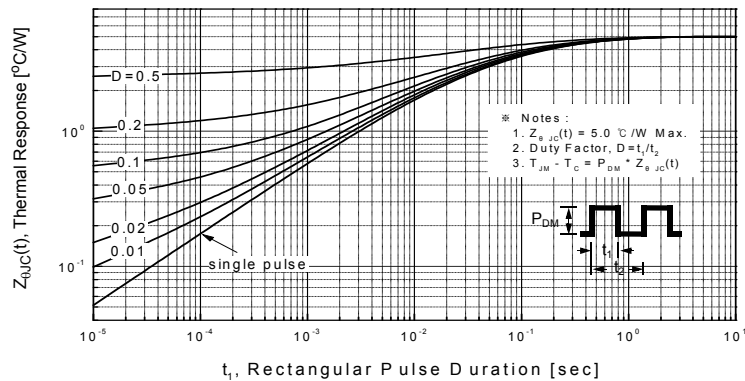


Figure 11. Transient Thermal Response Curve

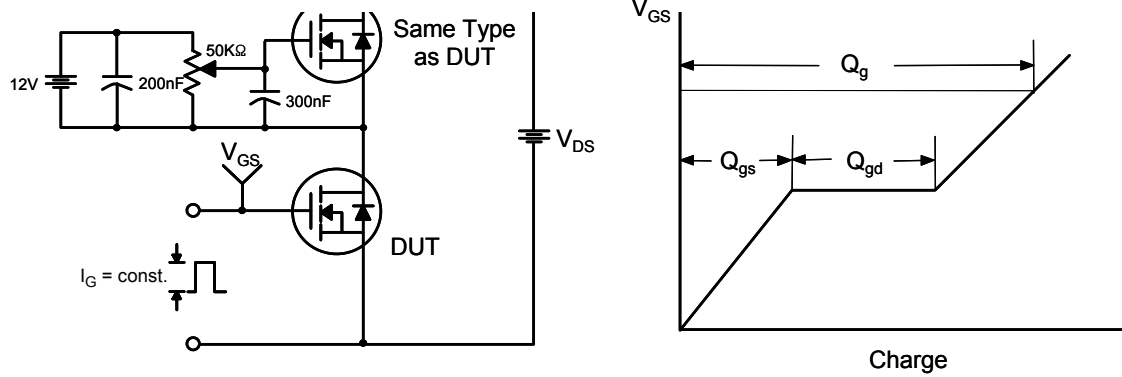


Figure 12. Gate Charge Test Circuit & Waveform

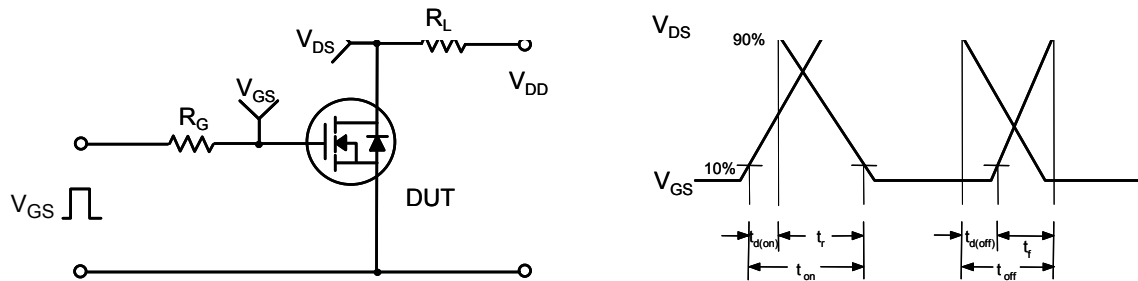


Figure 13. Resistive Switching Test Circuit & Waveforms

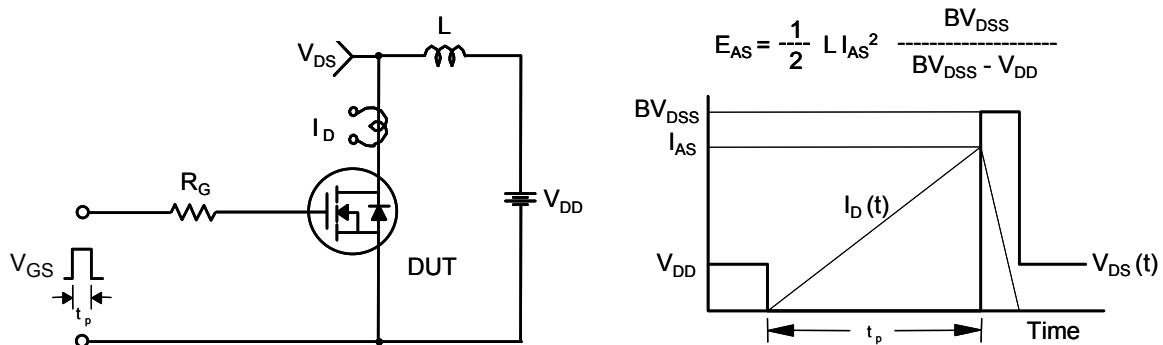
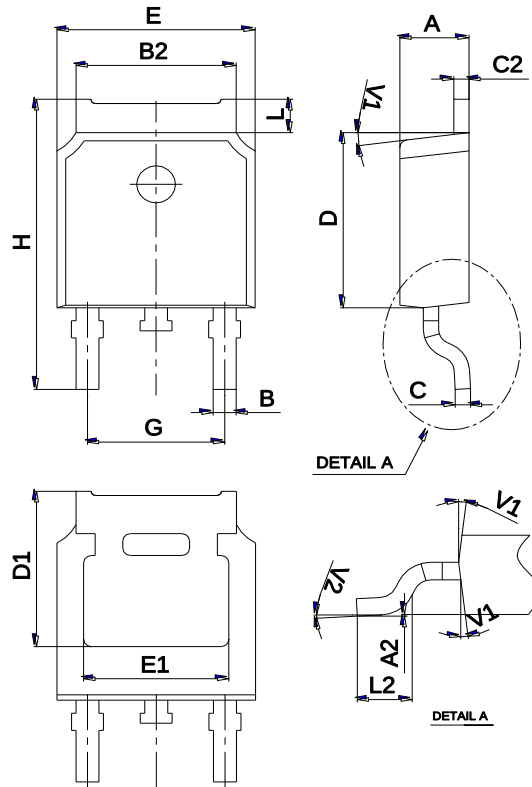


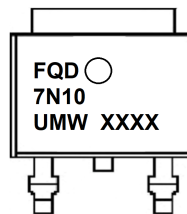
Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FQD7N10LTM	TO-252	2500	Tape and reel